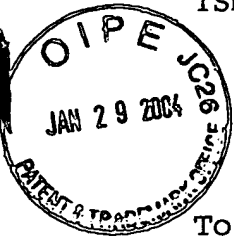


TSMC-02-130



January 5, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/692,030 10/23/03 |

Syun-Ming Jang et al.

IMPROVEMENT OF SiOC PROPERTIES AND  
ITS UNIFORMITY IN BULK FOR DAMASCENE  
APPLICATIONS

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.


The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 1/27/04

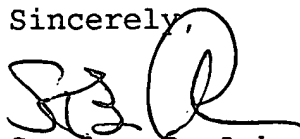
U.S. Patent 6,372,661 to Lin et al., "Method to Improve the Crack Resistance of CVD Low-K Dielectric Constant Material," describes SiOC films and post-treatments.

U.S. Patent 6,348,407 to Gupta et al., "Method to Improve Adhesion of Organic Dielectrics in Dual Damascene Interconnects," describes a plasma treatment of a low-k layer and an etch stop layer in a dual damascene process.

U.S. Patent 6,323,125 to Soo et al., "Simplified Dual Damascene Process Utilizing PPMSO as an Insulator Layer," describes a plasma treatment and PPMSO layer in a dual damascene process.

U.S. Patent 6,323,121 to Liu et al., "Fully Dry Post-Via-Etch Cleaning Method for a Damascene Process," describes a dual damascene process with etch stops and a plasma treatment.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a large, stylized circular flourish to the right.

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

Doctor Number (Optional)

Application Number

TSMC-02-130

10/692,030

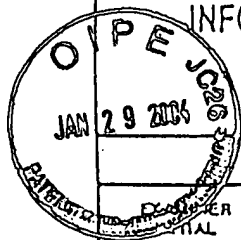
Applicant

'Syun-Ming Jang et al.

Filing Date

10/23/03

Qr ouo Ar Unit



## INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

## U. S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Portion or Pages, Etc.)

[illegible]

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.